Hot-hole cyclotron resonance in germanium in constant fields E1H

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The cyclotron-resonance spectra of hot holes in germanium have been measured at the wavelength $\lambda=1.65$ mm in a constant electric field $\mathbf{E} \perp \mathbf{H} \parallel [001]$. These are the first reported measurements of this type. The results reveal an overpopulation, effects of a nonparabolic light-hole dispersion law, a cutoff of the light-hole cyclotron resonance at $\mathbf{E} > 500$ V/cm, and the appearance of even harmonics of the heavy-hole cyclotron frequency.

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1. Hot-hole effects in germanium¹⁻⁵ have attracted interest because of the associated possibility of arranging a negative differential conductivity at wavelengths $2 \text{ mm} \geqslant \lambda \geqslant 0.05$ mm. This negative conductivity would result from an inversion of heavy holes in terms of the cyclotron-revolution energy in fields^{6,7} ElH and ElH (this is a classical analog of an inversion in terms of Landau levels) and from that inversion of direct optical transitions between heavy and light subbands which occurs in fields ElH and which is accompanied by an increase in the light-hole concentration to a point above its equilibrium value. Extensive information on the properties of holes in strong electric and magnetic fields can be obtained by the cyclotron-resonance method, which can be used to study light and heavy holes separately, to determine their concentrations and relaxation times in a constant electric field, to find effects resulting from the complex dispersion law, and, finally, to determine the absorption of germanium under conditions favoring a cyclotron-resonance negative differential conductivity.

In this letter we are reporting the first results of backward-wave-tube spectroscopy involving the cyclotron resonance of hot holes in Ge(Ga) at the wavelength $\lambda = 1.65$ mm, at $T \cong 10-30$ K, in electric fields up to 1 kV/cm.

2. In the experiments, the absorption of the millimeter-wave radiation from a backward-wave tube is measured in p-type germanium in a constant external magnetic field and a pulsed external electric field. The radiation propagates through a quasioptical system to a sample of square cross section, cut along [100] crystallographic axes. The sample is in a helium cryostat, at the center of a superconducting solenoid ($p \cong 4 \times 10^{13}$ cm⁻³, $N_A + N_D \sim 10^{14}$ cm⁻³). A plane face of the sample with an area of 4.7×4.7 mm² is oriented perpendicular to the magnetic field and to the wave vector of the millimeter-wave radiation. A voltage pulse ($\tau_p = 10~\mu s$, $f_{\rm rep} = 3.3$ Hz) applied to opposite faces with areas of 4.7×0.7 mm² ionizes acceptors, ¹⁾ giving rise to a modulation of the millimeter-wave radiation propagating through the sample. The output signal from an n-InSb detector below the sample is converted by a strobe integrator and recorded on a chart re-

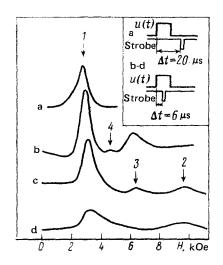


FIG. 1. The cyclotron-resonance spectra of p-Ge in crossed fields $E \perp H$. Arrow 1-Light holes; 2-4—second through fourth harmonics of the heavy-hole cyclotron resonance. u/l, V/cm; a-0 (T=30 K); b-90; c-330; d-780.

corder. The signal is stored in the strobe integrator at the time of arrival of a strobe pulse, synchronized with the voltage pulse.

3. Figure 1 shows some typical cyclotron-resonance spectra. Spectrum a is that of equilibrium holes; it was obtained by applying the strobe pulse immediately after the voltage pulse, u/l = 1300 V/cm (l = 0.47 cm is the length of the sample). This voltage pulse heated the lattice to $T \cong 30 \text{ K}$ (according to an estimate for adiabatic heating), so that essentially all the acceptors were ionized²⁾ (see the inset in Fig. 1). Spectra b-d correspond to coincident strobe and voltage pulses. In this case we can evaluate the ratio of the number of light holes at u = 0 ($p_{0,l}$) and $u \neq 0$ (p_l), taking the integrated intensity of the cyclotron-resonance line to be proportional to the hole concentration, $\int I(H)dH \sim p$.

The results show that the light-hole concentration begins to exceed its equilibrium value $(p_l/p_{0,l}>1)$ even at moderate electric fields, $u/l\sim 100$ V/cm (Fig. 2). Overpopulation effects in such fields have not been discussed or, apparently, observed previously. The overpopulation remains up to strong electric fields, at which $v_c\sim 0.3v_l\sim v_h$ [here $v_c=cE/H$, $v_{l,h}=(2\hbar\omega_0/m_{l,h})^{1/2}$, $m_{l,h}$ are the effective masses of the light and heavy holes, and $\hbar\omega_0$ is the energy of the optical phonon]. In such fields the overpopulation results from the intense scattering of heavy holes by optical phonons, which increases the rate of transitions from heavy to light holes; the number of inverse transitions is small because of the magnetization of the light holes.

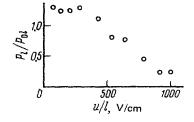


FIG. 2. Dependence of the concentration of "magnetized" light holes on the electric field. Here $p_{0,I}$ is the concentration of thermalized light holes at T = 30 K.

At fields u/l > 500 V/cm there is a decrease in the line intensity (a cutoff of the cyclotron resonance), because of an increase in the relative number of the holes which are "demagnetized," i.e., which reach an energy $\epsilon = \hbar \omega_0$ over a time shorter than the wave period, are scattered by a phonon, and thus do not participate in the cyclotron resonance. These events are accompanied by a decrease in the total number of light holes and by a disappearance of the overpopulation.⁹

- 4. With increasing electric field, the light-hole cyclotron-resonance line is observed to shift toward a stronger magnetic field: $\Delta H/H \sim 20\%$ at $v_c \sim 0.5 v_L$. Calculations show that this effect results from the deviation from a parabolic dispersion law for the light holes, which is manifested during the heating of the carriers. In a strong electric field some of the holes reach an energy $\epsilon \sim \hbar \omega_0$, at which their mass increases significantly, during the cyclotron-revolution period. At $v_c = 0.5v_l$, the cyclotron frequency of such holes is 8% lower than that of the holes which are revolving at energies $\epsilon \sim 3/2 kT = 0.1 \hbar \omega_0$ with T=30 K and E=0. The shift of the cyclotron-resonance peak in the electric field is caused by both a decrease in the average value of ω_c and a change in the line shape 10 caused by the dependence of ω_c on the hole oscillation energy. Estimates show that both of these effects shift the peak by 15%, if it is assumed that at $\epsilon < \hbar \omega_0$ the holes are localized around a trajectory in momentum space which passes through $\epsilon = 0$ (a principal trajectory), as a result of inelastic scattering by optical phonons. The good agreement of this estimate with experiment may be regarded as indirect evidence for the occurrence, at u/l > 500 V/cm, of a localized distribution of this sort, which is a distribution with an inversion in terms of the cyclotron-revolution energy. 11
- 5. The spectra in Fig. 1 reveal the appearance and intensification of the second and fourth harmonics of the heavy-hole cyclotron resonance, along with a decrease in the intensity of the third harmonic, with increasing electric field. We know that with $H \parallel [001]$ and E=0 the cyclotron-resonance spectrum of the heavy holes, with their anisotropic dispersion law, has only odd harmonics, because of the fourfold symmetry of the free-motion trajectories (Fig. 3). In an external electric field $E \parallel [100]$ this symmetry is disrupted; the intensities of the odd harmonics of the cyclotron revolution change; even harmonics appear; and we see evidence that the cyclotron revolution of the holes is not isochronous. And we see evidence that the cyclotron revolution of the holes occurs: $v_c \sim 0.1 v_h$ (Fig. 1). At $v_c > 0.5 v_h$, the nonisochronous revolution of the holes occurs: The second cyclotron harmonic of the heavy holes shifts 10% toward stronger magnetic fields at $v_c = 0.45 v_h$.

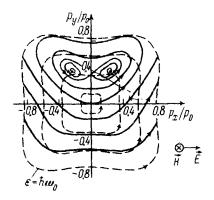


FIG. 3. Free-motion trajectories of heavy holes in the $p_z=0$ plane in momentum space for energies $\epsilon<\hbar\omega_0$. H || [001], E || [100], E/H = 0.1 V/(cm · Oe). Dashed curves-E=0. p_0 = $(2m_h\hbar\omega_0)^{1/2}$, where $m_h=0.32m_0$.

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It would be very interesting to see a further study of the hot-hole cyclotron resonance in pure germanium samples. We may expect that when an inversion in terms of the cyclotron-revolution energy is reached, the nonisochronous revolution of the holes [due to the nonparabolic nature of $\epsilon(p)$ in the case of the light holes or due to the anisotropy of $\epsilon(p)$ in the case of the heavy holes] will give rise to a cyclotron-revolution, negative-differential conductivity in crossed fields $\mathbf{E} \perp \mathbf{H}$.

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¹⁾It has been determined elsewhere that at T = 4.2 K there is essentially full ionization of the shallow impurities in p-Ge ($p \sim 10^{14}$ cm⁻³) in fields $E \sim 20$ -40 V/cm (see Ref. 1, for example).

²⁾The characteristic thermalization time for the holes at the end of the field pulse is $\leq 10^{-8}$ s. The subsequent cooling of the sample and the corresponding freezing of the holes occur in a time $\geq 10^{-3}$ s. The hole concentration after the field pulse depends on the energy imparted to the sample by the electric field; for pulses 10 μ s long, the hole concentration reaches saturation at u/l > 900 V/cm, as was verified from the cyclotron resonance.

^{1.} S. Komiyama and R. Spies, Phys. Rev. B 23, 6839 (1981).

V. A. Valov, V. A. Kozlov, L. S. Mazov, and I. M. Nefedov, Pis'ma Zh. Eksp. Teor. Fiz. 33, 608 (1981) [JETP Lett. 33, 591 (1981)].

^{3.} L. E. Vorob'ev, F. I. Osokin, V. I. Stafeev, and V. N. Tulupenko, Pis'ma Zh. Eksp. Teor. Fiz. 34, 125 (1981) [JETP Lett. 34, 118 (1981)].

^{4.} Yu. L. Ivanov, Pis'ma Zh. Eksp. Teor. Fiz. 34, 539 (1981) [JETP Lett. 34, 515 (1981)].

^{5.} V. I. Gavrilenko, V. N. Murzin, S. A. Stoklitskii, and A. P. Chebotarev, Pis'ma Zh. Eksp. Teor. Fiz. 35, 81 (1982) [JETP Lett. 35, 97 (1982)].

^{6.} A. A. Andronov, E. P. Dodin, and Z. F. Krasil'nik, Fiz. Tekh. Poluprovodn. 16, 212 (1982) [Sov. Phys. Semicond. (to be published)].

^{7.} A. A. Andronov, V. I. Gavrilenko, E. P. Dodin, Z. F. Krasil'nik, and M. D. Chernobrovtseva, Preprint No. 40, Institute of Applied Physics, Academy of Sciences of the USSR, Gor'kii, 1982.

^{8.} A. A. Andronov, V. A. Kozlov, L. S. Mazov, and V. N. Shastin, Pis'ma Zh. Eksp. Teor. Fiz. 30, 585 (1979) [JETP Lett. 30, 551 (1979)].

I. I. Vosilius and I. B. Levinson, Zh. Eksp. Teor. Fiz. 50, 1660 (1966) [Sov. Phys. JETP 28, 1104 (1966)];
I. I. Vosilyus, Fiz. Tverd. Tela (Leningrad) 11, 924 (1969) [Sov. Phys. Solid State 11, 755 (1969)].

^{10.} A. V. Gaponov, M. I. Petelin, V. K. Yulpatov, Izv. Vyssh. Uchebn. Zaved., Radiofiz. 10, 1414 (1967).

^{11.} A. A. Andronov, V. A. Valov, V. A. Kozlov, and L. S. Mazov, Fiz. Tverd. Tela (Leningrad) 22, 1275 (1980) [Sov. Phys. Solid State 22, 745 (1980)].

^{12.} A. A. Andronov, E. P. Dodin, G. M. Korobkov, Z. F. Krasil'nik, and M. D. Chernobrovtseva, Tezisy dokl. X soveshchaniya po teorii poluprovodnikov (Abstracts, Tenth Conference on the Theory of Semiconductors), Novoskbirsk, 1980, p. 29.